Document Number: IMEH0033-4 Production Datasheet V1.0

DC-3.3GHz, 4W, 28V LDMOS Fully matched PA Module

Description

The IMEH0033-4 is a 4-watt ,single stage integrated Power Amplifier Module, designed for broad band applications, with frequencies from DC to 3.3GHz. The module is 50 Ω input/output matched and requires minimal external components.



The module implements distributed power amplifier in form of multi chips, housed in cost effective plastic open cavity package, offers a much lower cost than traditional MMIC solutions.

Vds=28V, Idq=55mA, CW

Parameter	30MHz	0.5GHz	1.0GHz	1.5GHz	2.0GHz	2.5GHz	3.0GHz	3.3GHz	3.6GHz	Units
Linear Gain	17. 3	16.6	16.5	15. 9	15.8	16. 2	16. 2	15.6	15. 1	dB
Pout@Pin=23dBm	6.8	6. 4	5. 9	4. 9	4.8	5. 6	5. 1	4. 4	3. 2	W
Gain@Pin=23dBm	15. 3	15.0	14. 7	13. 9	13.8	14. 4	14. 1	13. 4	12.0	dB
Eff@ Pin=23dBm	71	57	43	37	37	47	45	43	35	%

Product Features

• Operating Frequency Range: DC-3.3GHz

• Operating Drain Voltage: +28 V

• 50 Ω Input/Output

• Psat: ≥4W

• Small signal gain:>15dB, Power gain:>13dB

• Minimum efficiency:>30%

• 6x10 mm Surface Mount Package

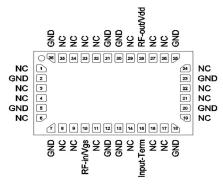
• Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

• Much lower cost than GaN-based ultrawide band PA, due to LDMOS technology used

Applications

- Ultra Broadband Amplifiers
- Fiber Drivers
- Test Instrumentation
- EMC Amplifier Drivers
- 2-way Radios

Pin Configuration and Description



Top View



Document Number: IMEH0033-4 Production Datasheet V1.0

Pin No.	Symbol	Description	
28	RFout/Vdd	Transistor 1, Drain Bias & RF Output	
10	RFin/Vgs	Transistor 1, RF Input &Gate Bias	
15	Input-Term	Transistor 1, Input 50 ohm term	
Others	NC	No connection	
2,5,7,12, 13,18,20,23,25, 30, 31,36 Package Base	GND	DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under Pkg Base will result in excessive junction temperatures causing permanent damage.	

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
DrainSource Voltage	V _{DSS}	65	Vdc
GateSource Voltage	V_{GS}	-10 to +10	Vdc
Operating Voltage	V _{DD}	+32	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	Tc	+150	°C
Operating Junction Temperature	T₃	+200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	Dava	G	°C/W
T _C = 87°C, T _J =175°C, DC test	Rejc	6	-0/00

Table 3. Electrical Characteristics

Parameter	Condition	Min	Тур	Max	Unit
Frequency Range		30		3300	MHz
Power Gain @ Psat		13			dB
P _{SAT}		36			dBm
Drain Efficiency @ P _{SAT}		30			%
Unless otherwise noted: TA = 25°C, V _{DD} =28 V, Pulse Width=100 us, Duty cycle=10%					

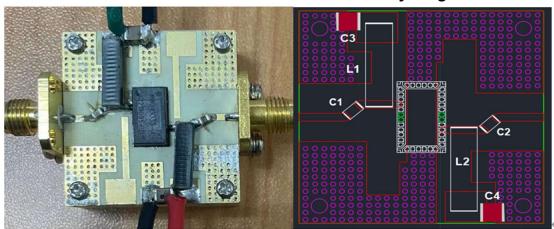
Load Mismatch of per Section (On Test Fixture, 50 ohm system): $V_{DD} = 28 \text{ V}$, $I_{DQ} = 55 \text{ mA}$, f = 3.3 GHz

VSWR 10:1 at Psat pulse CW Output Power	No Device Degradation
---	-----------------------



Document Number: IMEH0033-4 Production Datasheet V1.0

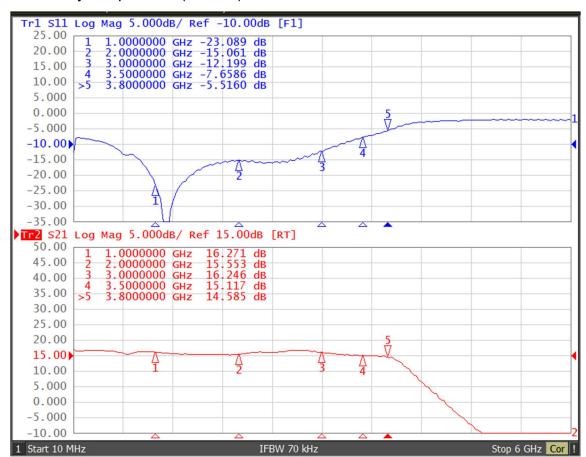
Reference Circuit of Test Fixture Assembly Diagram



		Part NO.	Vendor
C3,C4	10uF 100V chip Capacitor	C5750X7S2A106M230KB	TDK
C1,C2	50V 1uF Chip Capacitor	GRM21BR71H105KA12L	muRata
L1,L2	1.3 uH 4.2A Inductor	4310LC-132KEC	Coilcraft
PCB	RO4350B,20mil,er=3.48		

TYPICAL CHARACTERISTICS

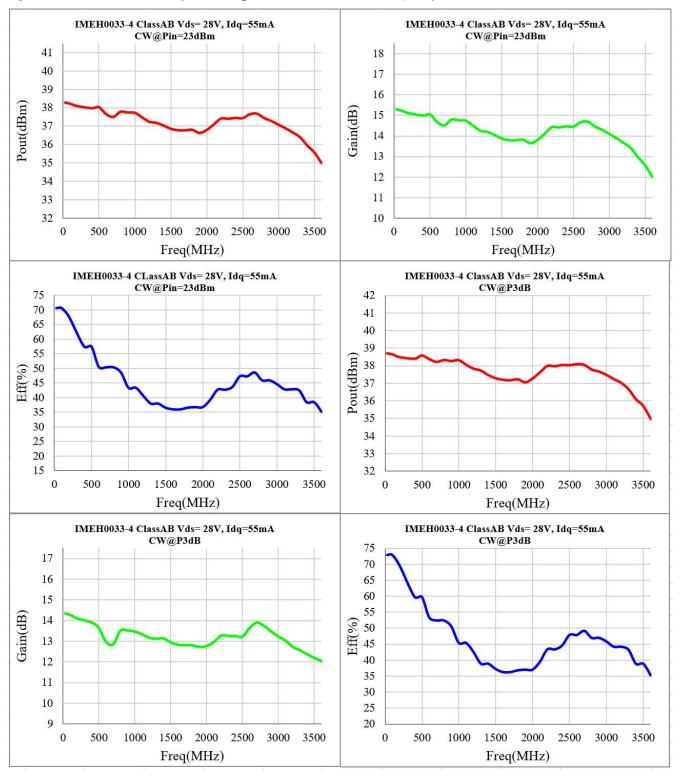
Figure 1. Network analyzer output S11/S21 (Pin=0dBm)





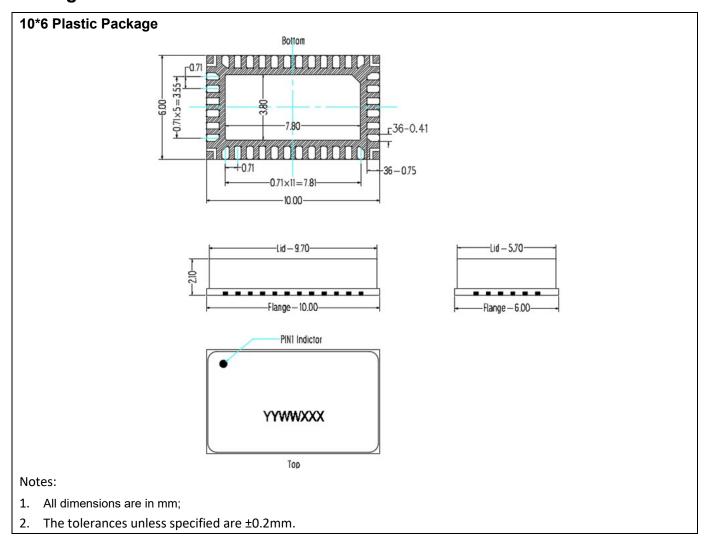
Document Number: IMEH0033-4 Production Datasheet V1.0

Figure. Power Gain and, efficiency and Pout @Pin=23dBm ,and P3dB vs. Frequency

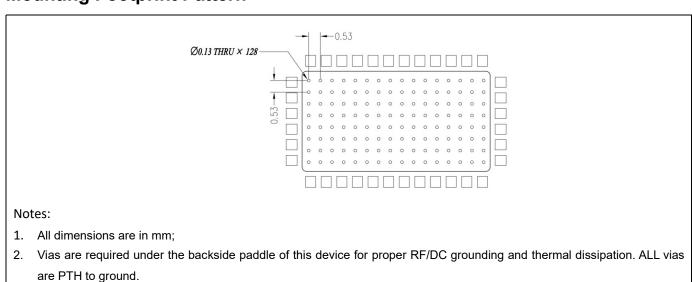


Document Number: IMEH0033-4 Production Datasheet V1.0

Package Dimensions



Mounting Footprint Pattern



Document Number: IMEH0033-4 Production Datasheet V1.0

Revision history

Table 6. Document revision history

Date	Revision	Datasheet Status
2022/12/9	Rev 1.0	Production Datasheet

Application data based on ZHH-22-07

Disclaimers

Specifications are subject to change without notice. Innogration believes the information contained within this data sheet to be accurate and reliable. However, no responsibility is assumed by Innogration for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Innogration . Innogration makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. "Typical" parameters are the average values expected by Innogration in large quantities and are provided for information purposes only. These values can and do vary in different applications and actual performance can vary over time. All operating parameters should be validated by customer's technical experts for each application. Innogration products are not designed, intended or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Innogration product could result in personal injury or death or in applications for planning, construction, maintenance or direct operation of a nuclear facility. For any concerns or questions related to terms or conditions, pls check with Innogration and authorized distributors Copyright © by Innogration (Suzhou) Co.,Ltd.